

DANIEL JOHNSON, JR. (SBN 57409)
BRETT M. SCHUMAN (SBN 189247)
MORGAN, LEWIS & BOCKIUS LLP
One Market, Spear Street Tower
San Francisco, CA 94105-1126
Tel: 415.442.1000
Fax: 415.442.1001
djjohnson@morganlewis.com
bschuman@morganlewis.com

ANDREW J. WU (SBN 214442)
DAVID V. SANKER (SBN 251260)
MORGAN, LEWIS & BOCKIUS LLP
2 Palo Alto Square
3000 El Camino Real, Suite 700
Palo Alto, CA 94306-2122
Tel: 650.843.4000
Fax: 650.843.4001
awu@morganlewis.com
dsanker@morganlewis.com

Attorneys for Plaintiffs and Counterdefendants
ALPHA & OMEGA SEMICONDUCTOR,
LTD.
ALPHA & OMEGA SEMICONDUCTOR,
INC.

UNITED STATES DISTRICT COURT
NORTHERN DISTRICT OF CALIFORNIA
SAN FRANCISCO DIVISION

ALPHA & OMEGA SEMICONDUCTOR,
LTD., a Bermuda corporation; and
ALPHA & OMEGA SEMICONDUCTOR,
INC., a California corporation,

Plaintiffs and Counterdefendants,

v.

FAIRCHILD SEMICONDUCTOR
CORP., a Delaware corporation,

Defendant and Counterclaimant.

AND RELATED COUNTERCLAIMS.

Case No. C 07-2638 JSW
(Consolidated with Case No. C-07-2664 JSW)

**DECLARATION OF YALEI SUN IN
SUPPORT OF ALPHA & OMEGA
SEMICONDUCTOR, LTD AND ALPHA &
OMEGA SEMICONDUCTOR, INC'S
OPPOSITION CLAIM CONSTRUCTION
BRIEF PURSUANT TO CIVIL L. R.
16-11(D)(1)**

Date: June 4, 2008
Time: 2:00 PM
Place: Courtroom 2, 17th Floor
Judge: Honorable Jeffrey S. White

1 I, Yalei Sun, hereby declare as follows:

2 1. I am an associate at the law firm of Morgan, Lewis & Bockius LLP, 2 Palo Alto
3 Square Avenue, 3000 El Camino Real, Suite 700, Palo Alto, California 94306, and a member in
4 good standing of the Bar of the State of California. Morgan, Lewis & Bockius LLP has been
5 retained as trial counsel for the Plaintiffs and Counterdefendants Alpha & Omega Semiconductor,
6 LTD and Alpha & Omega Semiconductor, Inc., in the present action. I submit this declaration in
7 support of Alpha & Omega Semiconductor, LTD and Alpha & Omega Semiconductor, Inc.'s
8 Opposition Claim Construction Brief Pursuant to Civil L. R. 16-11(d)(1).

9 2. Attached hereto as Exhibit 1 is a true and correct copy of United States Patent No.
10 6,429,481.

11 3. Attached hereto as Exhibit 2 is a true and correct copy of United States Patent No.
12 6,710,406.

13 4. Attached hereto as Exhibit 3 is a true and correct copy of United States Patent No.
14 6,521,497.

15 5. Attached hereto as Exhibit 4 is a true and correct copy of United States Patent No.
16 6,828,195.

17 6. Attached hereto as Exhibit 5 is a true and correct copy of United States Patent No.
18 7,148,111.

19 7. Attached hereto as Exhibit 6 is a true and correct copy of United States Patent No.
20 6,818,947.

21 8. Attached hereto as Exhibit 7 is a true and correct copy of the Prosecution History
22 of U.S. Patent No. 6,429,481, Application as Filed.

23 9. Attached hereto as Exhibit 8 is a true and correct copy of the Prosecution History
24 of U.S. Patent No. 6,429,481, Amendment received by the Patent Office November 8, 1999.

25 10. Attached hereto as Exhibit 9 is a true and correct copy of the Prosecution History
26 of U.S. Patent No. 6,429,481, Amendment received by the Patent Office September 5, 2000.

27 11. Attached hereto as Exhibit 10 is a true and correct copy of the Prosecution History
28 of U.S. Patent No. 6,429,481, Office Action dated December 5, 2000.

12. Attached hereto as Exhibit 11 is a true and correct copy of the Prosecution History of U.S. Patent No. 6,429,481, Amendment received by the Patent Office June 7, 2001.¹

13. Attached hereto as Exhibit 12 is a true and correct copy of the Prosecution History of U.S. Patent No. 6,429,481, Amendment received by the Patent Office December 31, 2001.

14. Attached hereto as Exhibit 13 is a true and correct copy of the Appeal Brief for Application No. 10/630,249 dated November 3, 2005.

15. Attached hereto as Exhibit 14 is a true and correct copy of pages 63 – 108 of S.M. Sze, *Physics of Semiconductor Devices* (1981) (describing abrupt and linearly graded P-N junctions and the differences between the two).

16. Attached hereto as Exhibit 15 is a true and correct copy of page 1 of THE IEEE STANDARD DICTIONARY OF ELECTRICAL AND ELECTRONICS TERMS (6th ed. 1997) (defining “abrupt junction”).

17. Attached hereto as Exhibit 16 is a true and correct copy of page 1 of the MCGRAW-HILL ELECTRONICS DICTIONARY (5th ed. 1994) (defining “abrupt junction”).

18. Attached hereto as Exhibit 17 is a true and correct copy of pages 63 – 70, and 298 of Sorab K. Ghandhi, *Semiconductor Power Devices* (1977) (describing field termination structures and identifying a high-low junction as an ohmic contact where current flows easily in either direction).

19. Attached hereto as Exhibit 18 is a true and correct copy of pages 210, 446 – 455 of R.W. Warner and G.L. Grung, *TRANSISTORS : Fundamentals for the Integrated Circuit Engineer* (1990) (identifying a high-low junction as an ohmic contact where current flows easily on either direction).

20. Attached hereto as Exhibit 19 is a true and correct copy of pages 116 – 119 of B. Jayant Baliga, *Modern Power Devices* (1992) (describing the operation of field plates).

21. Attached hereto as Exhibit 20 is a true and correct copy of United States Patent No. 5,233,215 (cited by the ‘947 patent for its description of trenched field plates).

¹Note that the original page 4 of this document was apparently missing from the file wrapper at the Patent Office. The current copy of page 4 was produced by Fairchild from its own photocopy of the same document in response to AOS’s request.

22. Attached hereto as Exhibit 21 is a true and correct copy of page 2065 of the MCGRAW-HILL DICTIONARY OF SCIENTIFIC AND TECHNICAL TERMS (5th ed. 1994) (defining “trench”).

23. Attached hereto as Exhibit 22 is a true and correct copy of page 1259 of Merriam Webster’s Collegiate Dictionary (10th ed. 1997) (defining “trench”).

24. Attached hereto as Exhibit 23 is a true and correct copy of the Prosecution History of U.S. Patent No. 6,818,947, Amendment received at the Patent Office July 21, 2003.

25. Attached hereto as Exhibit 24 is a true and correct copy of the Prosecution History of U.S. Patent No. 6,818,947, Amendment received at the Patent Office December 29, 2003.

26. Attached hereto as Exhibit 25 is a true and correct copy of pages 0 – 3, 204 – 212 of AOS’s Supplemental Preliminary Invalidity Contentions for U.S. Patent Nos. 6,429,481, 6,521,497, 6,710,406, 6,828,195, 7,148,111, and 6,818,947 Pursuant to Patent L.R. 3-3, served March 3, 2008.

27. Attached hereto as Exhibit 26 is a true and correct copy of the definition of “Finite element analysis” from Wikipedia, ([http://en.wikipedia.org/wiki/Finite element analysis](http://en.wikipedia.org/wiki/Finite_element_analysis)), downloaded January 7, 2008.

28. Attached hereto as Exhibit 27 is a true and correct copy of Exhibit 2 of Fairchild’s Preliminary Infringement Contentions.

29. Attached hereto as Exhibit 28 is a true and correct copy of pages 0 – 3, 207 – 209 of AOS’s Preliminary Invalidity Contentions For U.S. Patent Nos. 6,429,481, 6,521,497, 6,710,406, 6,828,195, 7,148,111, and 6,818,947 Pursuant to Patent L.R. 3-3, served November 29, 2007.

////

////

////

////

////

////

1
2
3
4
5
6
7
8
9
10
11
12
13
14
15
16
17
18
19
20
21
22
23
24
25
26
27
28

I declare under of penalty of perjury that the foregoing is true and correct. Executed in
Palo Alto, California.

Dated: March 27, 2008

by


Yalei Sun